



IXTA3N120TRL Information



For Reference Only

Part Number IXTA3N120TRL

Manufacturer IXYS

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 1200V 3A TO-263

Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IXTA3N120TRL Specifications

Manufacturer Part Number IXTA3N120TRL Manufacturer IXYS Category Discrete Semiconductor Products Fackage To-263-3, D2Pak (2 Leads + Tab), TO-263AB Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1200V Current - Continuous Drain (Id) @ 25°C 3A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 42nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1350pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 200W (Tc) Rds On (Max) @ Id, Vgs 4.5 Ohm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-263 (IXTA) Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB		
Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-263-3, D2Pak (2 Leads + Tab), TO-263AB Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1200V Current - Continuous Drain (Id) @ 25°C 3A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id Sty @ 250µA Gate Charge (Qg) (Max) @ Vgs 42nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1350pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.5 Ohm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-263 (IXTA) Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Manufacturer Part Number	IXTA3N120TRL
Package To-263-3, D2Pak (2 Leads + Tab), TO-263AB Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1200V Current - Continuous Drain (Id) @ 25°C 3A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 42nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1350pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 200W (Tc) Rds On (Max) @ Id, Vgs 4.5 Ohm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-263 (IXTA) Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Manufacturer	IXYS
Package Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1200V Current - Continuous Drain (Id) @ 25°C 3A (Tc) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Sty @ 250µA Gate Charge (Qg) (Max) @ Vds 1350pF @ 25V Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.5 Ohm @ 1.5A, 10V Operating Temperature Supplier Device Package TO-263 (IXTA) Package / Case N-Channel N-Chann	Category	Discrete Semiconductor Products
Series - FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 1200V Current - Continuous Drain (Id) @ 25°C 3A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 42nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1350pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 200W (Tc) Rds On (Max) @ Id, Vgs 4.5 Ohm @ 1.5A, 10V Operating Temperature 55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-263 (IXTA) Package / Case Totology (Max) (Mose Mose Mose Mose Mose Mose Mose Mose		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)1200VCurrent - Continuous Drain (Id) @ 25°C3A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs42nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1350pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)200W (Tc)Rds On (Max) @ Id, Vgs4.5 Ohm @ 1.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-263 (IXTA)Package / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Package	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)1200VCurrent - Continuous Drain (Id) @ 25°C3A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs42nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1350pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)200W (Tc)Rds On (Max) @ Id, Vgs4.5 Ohm @ 1.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-263 (IXTA)Package / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Series	-
Drain to Source Voltage (Vdss)1200VCurrent - Continuous Drain (Id) @ 25°C3A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs42nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1350pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)200W (Tc)Rds On (Max) @ Id, Vgs4.5 Ohm @ 1.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-263 (IXTA)Package / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Sv @ 250μA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package TO-263 (IXTA) Package / Case 3A (Tc) 42pC @ 250μA 42pC @ 10V 1350pF @ 25V 42pV FET Feature	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id St @ 250μA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.5 Ohm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-263 (IXTA) Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Drain to Source Voltage (Vdss)	1200V
Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs 42nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1350pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 200W (Tc) Rds On (Max) @ Id, Vgs 4.5 Ohm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-263 (IXTA) Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Current - Continuous Drain (Id) @ 25°C	3A (Tc)
Gate Charge (Qg) (Max) @ Vgs 42nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 1350pF @ 25V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 200W (Tc) Rds On (Max) @ Id, Vgs 4.5 Ohm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-263 (IXTA) Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds 1350pF @ 25V Vgs (Max) #20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.5 Ohm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-263 (IXTA) Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Vgs(th) (Max) @ Id	5V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)200W (Tc)Rds On (Max) @ Id, Vgs4.5 Ohm @ 1.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-263 (IXTA)Package / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Gate Charge (Qg) (Max) @ Vgs	42nC @ 10V
FET Feature - Power Dissipation (Max) 200W (Tc) Rds On (Max) @ Id, Vgs 4.5 Ohm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-263 (IXTA) Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Input Capacitance (Ciss) (Max) @ Vds	1350pF @ 25V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 4.5 Ohm @ 1.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount Supplier Device Package TO-263 (IXTA) Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs4.5 Ohm @ 1.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeSurface MountSupplier Device PackageTO-263 (IXTA)Package / CaseTO-263-3, D2Pak (2 Leads + Tab), TO-263AB	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Surface Mount TO-263 (IXTA) Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Power Dissipation (Max)	200W (Tc)
Mounting Type Surface Mount Supplier Device Package TO-263 (IXTA) Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Rds On (Max) @ Id, Vgs	4.5 Ohm @ 1.5A, 10V
Supplier Device Package TO-263 (IXTA) Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-263-3, D2Pak (2 Leads + Tab), TO-263AB	Mounting Type	Surface Mount
	Supplier Device Package	TO-263 (IXTA)
Report errors?	Package / Case	TO-263-3, D2Pak (2 Leads + Tab), TO-263AB
		Report errors?

IXTA3N120TRL Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IXTA3N120TRL Payment Methods



















IXTA3N120TRL Shipping Methods













If you have any question about IXTA3N120TRL, please do not hesitate to contact us!

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